HOA2307

P-Channel MOSFET

FEATURES

- Lower on-resistance
- Reliable and Rugged

1.Gate
2.Source
3.Drain

SOT-23

Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-source Voltage	V_{GS}	±20	V
Drain Current (Continuous) [a]	I_D	-2.7	A
Total Power Dissipation @TA=25°C [b]	P_D	1.1	W
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 to +150	°C
Thermal Resistance Junction to Ambient (PCB mounted)	$R_{\theta JA}$	114	°C/W

Electrical Characteristics (TA=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-30			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-1		-3	
Gate-Source Leakage	I_{GSS}	V_{DS} =0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-30V, V_{GS} =0V			-1	μA
		V_{DS} =-30V, V_{GS} =0V, T_J=55℃			-10	
Drain-Source On-State Resistance[c]	$R_{DS(on)}$	V_{GS} =-4.5V, I_D =-2.5A		0.110	0.138	Ω
		V_{GS} =-10V, I_D =-3.5A		0.073	0.088	
Forward Transconductance[c]	g_{fs}	V_{DS} =-10V, I_D =-3.5A		7		S
Dynamic[d]						
Input Capacitance	C_{iss}	V_{DS} =-15V,V_{GS} =0V,f =1MHz		340		pF
Output Capacitance	C_{oss}			67		
Reverse Transfer Capacitance	C_{rss}			51		
Total Gate Charge	Q_g	V_{DS} =-15V,V_{GS} =-4.5V, I_D =-2.5A		4.1	6.2	nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			1.8		
Gate Resistance	R_g	f =1MHz		10		Ω

HOA2307

Turn-On Delay Time	$t_{d(on)}$	V_{DD}=-15V, R_L=15Ω, I_D =-1A, V_{GEN}=-4.5V,Rg=1Ω		40	60	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{d(off)}$			20	40	
Fall Time	t_f			17	30	
Drain-source Body diode characteristics						
Body Diode Voltage	V_{SD}	I_S=-0.75A, ,V_{GS} =0		-0.8	-1.2	V

Notes:

a. t=5s.

b. Surface mounted on 1” ×1” FR4 board.

c. Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.

d. Guaranteed by design, not subject to production testing.

HOA2307 Typical Characteristics